

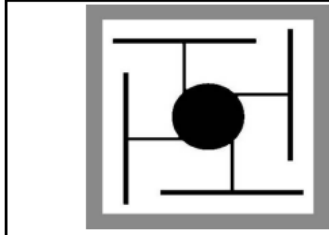


LED Chip red

ELC-630-15

Rev. 03, 2017

Radiation	Type	Electrodes
Red	AlGaInP / Si	P (anode) up



- High luminous intensity
- Thin film structure
- Typ. dimension 350±25 µm
- Typ. thickness 100±15 µm

Absolute Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Symbol	Typ	Unit
Forward DC current	I _F	≤70	mA
Reverse voltage	V _R	≤10	V
Junction temperature	T _J	125	°C
Storage temperature	T _{stg}	-40 ~ +85	°C

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =10 µA	V _F	1.3			V
Forward voltage	I _F =20 mA	V _F		2.1	2.5	V
Reverse current	V _R = 10V	I _R			5	µA
Luminous intensity*	I _F =20 mA	I _V		600		mcd
Peak wavelength	I _F =20 mA	λ _p		631		nm
Dominant wavelength	I _F =20 mA	λ _p		624		nm
FWHM	I _F =20 mA	Δλ _{0.5}		20		nm

*Measured on bare chip on TO-18 header